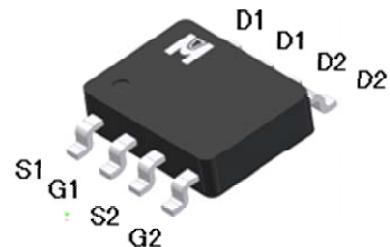
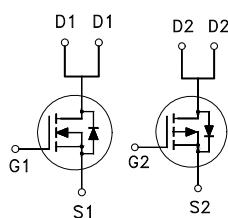


N & P-Channel Logic Level Enhancement Mode Field Effect Transistor

Product Summary:

	N-CH	P-CH
BV _{DSS}	40V	-40V
R _{DSON} (MAX.)	22mΩ	42mΩ
I _D	7.5A	-6A



Pb-Free Lead Plating & Halogen Free



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS		UNIT
Gate-Source Voltage		V _{GS}	N-CH	P-CH	V
			±20	±20	
Continuous Drain Current	T _A = 25 °C	I _D	7.5	-6	A
	T _A = 70 °C		6	-5	
Pulsed Drain Current ¹		I _{DM}	30	-24	
Power Dissipation	T _A = 25 °C	P _D	2		W
	T _A = 70 °C		1.3		
Operating Junction & Storage Temperature Range		T _j , T _{stg}	-55 to 150		°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Case	R _{θJC}		25	°C / W
Junction-to-Ambient ³	R _{θJA}		62.5	

¹Pulse width limited by maximum junction temperature.

²Duty cycle ≤ 1%

³62.5°C / W when mounted on a 1 in² pad of 2 oz copper.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{GS} = 0V, I_D = 250\mu\text{A}$	N-CH	40		V
		$V_{GS} = 0V, I_D = -250\mu\text{A}$	P-CH	-40		
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	N-CH	1.5	2.0	3.0
		$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$	P-CH	-1.5	-2.0	-3.0
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$	N-CH			± 100
		$V_{DS} = 0V, V_{GS} = \pm 20V$	P-CH			± 100
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 32V, V_{GS} = 0V$	N-CH			1
		$V_{DS} = -32V, V_{GS} = 0V$	P-CH			-1
		$V_{DS} = 30V, V_{GS} = 0V, T_J = 125^\circ\text{C}$	N-CH			25
		$V_{DS} = -30V, V_{GS} = 0V, T_J = 125^\circ\text{C}$	P-CH			-25
On-State Drain Current ¹	$I_{D(\text{ON})}$	$V_{DS} = 5V, V_{GS} = 10V$	N-CH	7.5		A
		$V_{DS} = -5V, V_{GS} = -10V$	P-CH	-6		
Drain-Source On-State Resistance ¹	$R_{DS(\text{ON})}$	$V_{GS} = 10V, I_D = 7.5A$	N-CH		20	22
		$V_{GS} = -10V, I_D = -6A$	P-CH		37	42
		$V_{GS} = 4.5V, I_D = 5A$	N-CH		33	40
		$V_{GS} = -4.5V, I_D = -4A$	P-CH		70	85
Forward Transconductance ¹	g_{fs}	$V_{DS} = 5V, I_D = 7.5A$	N-CH		20	S
		$V_{DS} = -5V, I_D = -6A$	P-CH		10	
DYNAMIC						
Input Capacitance	C_{iss}	$N\text{-CH}$	N-CH		536	pF
		$V_{GS} = 0V, V_{DS} = 20V, f = 1\text{MHz}$	P-CH		810	
Output Capacitance	C_{oss}	$P\text{-CH}$	N-CH		83	pF
		$V_{GS} = 0V, V_{DS} = -20V, f = 1\text{MHz}$	P-CH		94	
Reverse Transfer Capacitance	C_{rss}	$N\text{-CH}$	N-CH		66	pF
		$P\text{-CH}$	P-CH		72	

Total Gate Charge ^{1,2}	Q_g	N-CH $V_{DS} = 20V, V_{GS} = 10V,$ $I_D = 7.5A$ P-CH $V_{DS} = -20V, V_{GS} = -10V,$ $I_D = -6A$	N-CH		14.5		nC
Gate-Source Charge ^{1,2}	Q_{gs}		P-CH		15		
Gate-Drain Charge ^{1,2}	Q_{gd}		N-CH		2.1		
Turn-On Delay Time ^{1,2}	$t_{d(on)}$		P-CH		2.6		
Rise Time ^{1,2}	t_r		N-CH		4.3		
Turn-Off Delay Time ^{1,2}	$t_{d(off)}$		P-CH		3.1		
Fall Time ^{1,2}	t_f	N-CH $V_{DS} = 10V,$ $I_D = 1A, V_{GS} = 10V, R_{GS} = 6\Omega$ P-CH $V_{DS} = -10V,$ $I_D = -1A, V_{GS} = -10V, R_{GS} = 6\Omega$	N-CH		5		nS
			P-CH		12		
			N-CH		10		
			P-CH		15		
			N-CH		15		
			P-CH		25		
			N-CH		12		
			P-CH		15		

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_c = 25^\circ C$)

Continuous Current	I_S	$I_F = I_S, V_{GS} = 0V$	N-CH			7.5	A	
Pulsed Current ³	I_{SM}		P-CH			-6		
Forward Voltage ¹	V_{SD}		N-CH			20	V	
			P-CH			-20		
			N-CH			1.3	V	
			P-CH			-1.3		

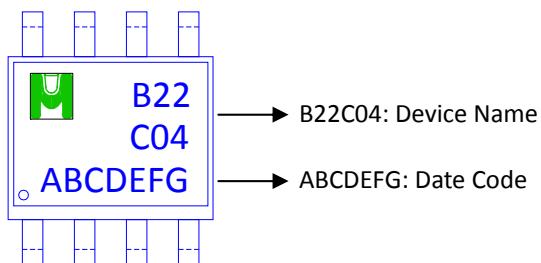
¹Pulse test : Pulse Width $\leq 300 \mu\text{sec}$, Duty Cycle $\leq 2\%$.

²Independent of operating temperature.

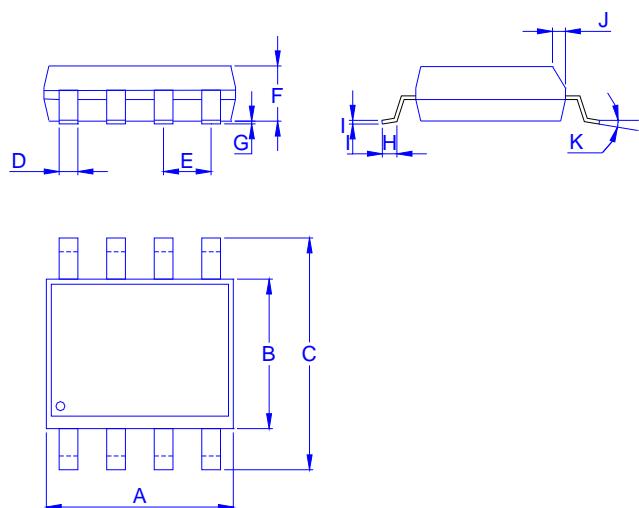
³Pulse width limited by maximum junction temperature.

Ordering & Marking Information:

Device Name: EMB22C04G for SOP-8



Outline Drawing

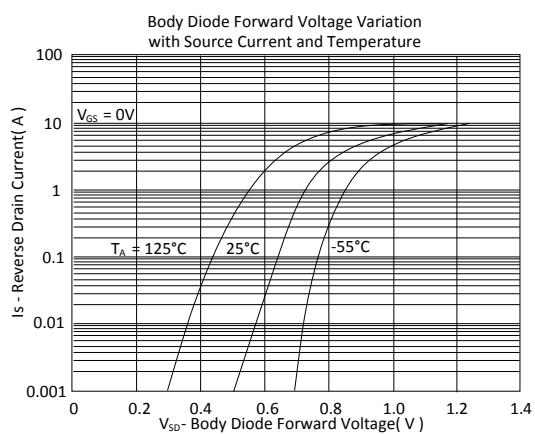
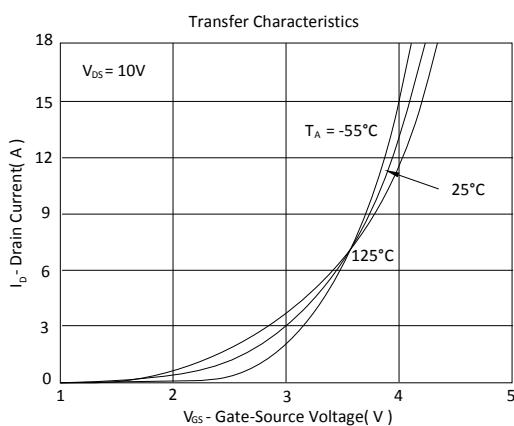
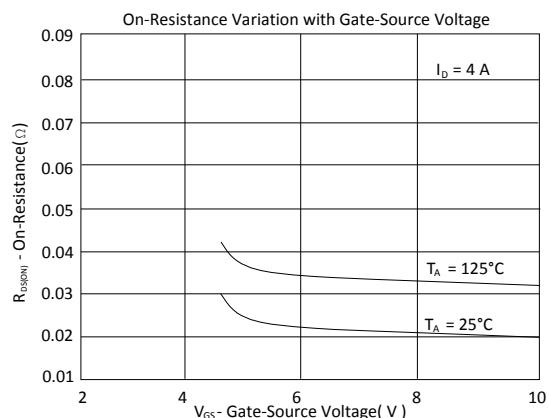
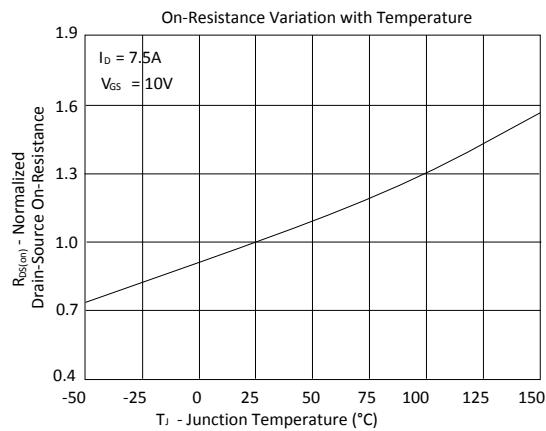
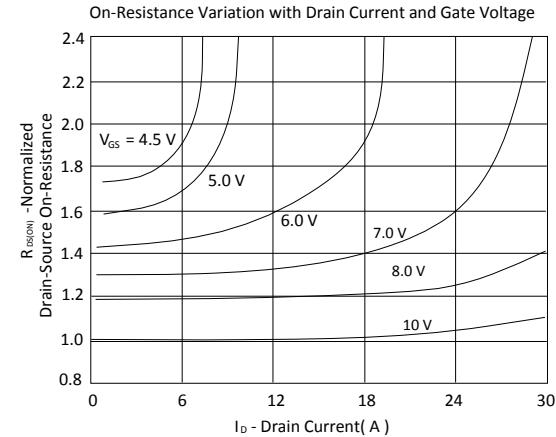
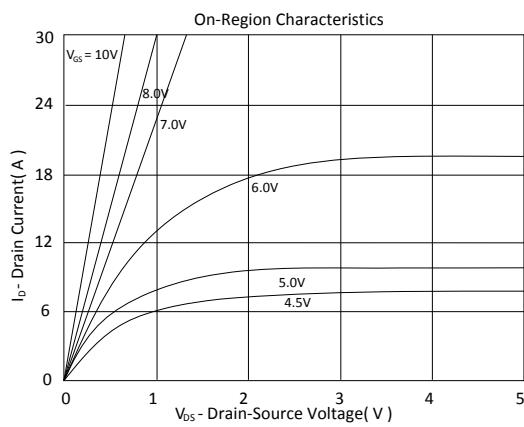


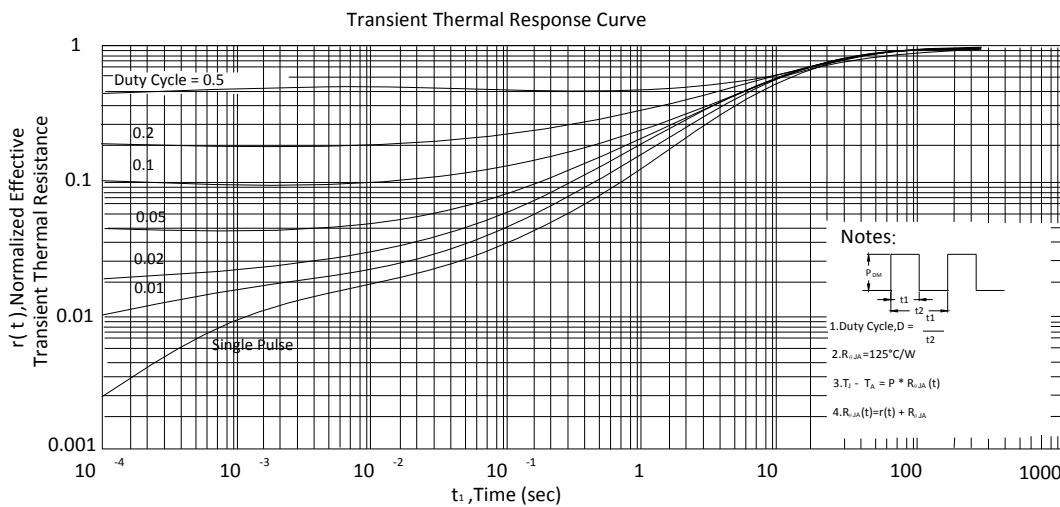
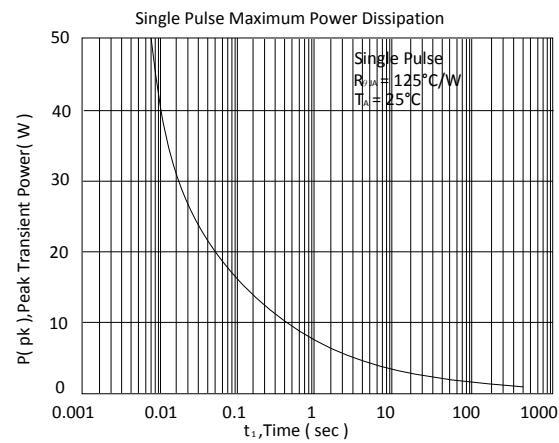
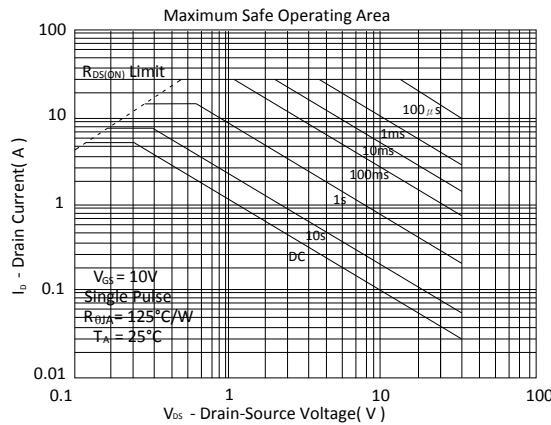
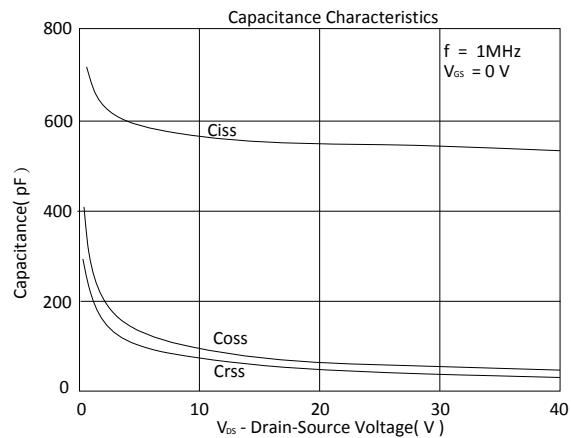
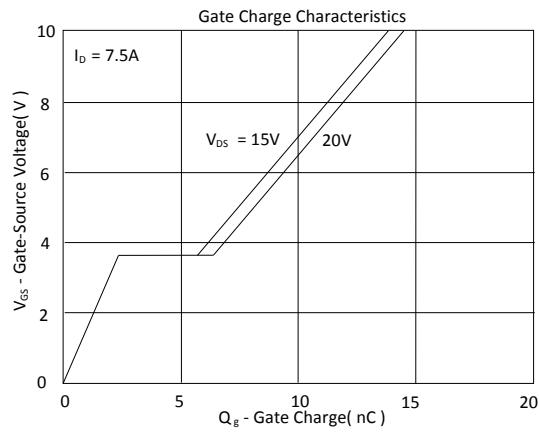
Dimension in mm

Dimension	A	B	C	D	E	F	G	H	I	J	K
Min.	4.70	3.70	5.80	0.33		1.20	0.08	0.40	0.19	0.25	0°
Typ.					1.27						
Max.	5.10	4.10	6.20	0.51		1.62	0.28	0.83	0.26	0.50	8°



N-Channel





P-Channel

